

MOS FIELD EFFECT TRANSISTOR 2SK4212A

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4212A is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

FEATURES

Low on-state resistance

 $R_{DS(on)1} = 8.0 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 10 \text{ V, I}_D = 30 \text{ A)}$

 $R_{DS(on)2}$ = 14 m Ω MAX. (VGS = 4.5 V, ID = 20 A)

• Low total gate charge

Q_G = 24 nC TYP. (V_{DD} = 15 V, V_{GS} = 10 V, I_D = 30 A)

- 4.5 V drive available
- Avalanche capability ratings

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SK4212A-ZK-E1-AY Note	Duro Sp (Tip)	Tano 2500 p/rool	TO 252 (MD 27K) tup 0.27 c
2SK4212A-ZK-E2-AY Note	Pure Sn (Tin)	Tape 2500 p/reel	TO-252 (MP-3ZK) typ. 0.27 g

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	30	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±48	Α
Drain Current (pulse) Note1	D(pulse)	±125	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	35	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note2	las	16	Α
Single Avalanche Energy Note2	Eas	25	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 0.1 mH

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(TO-252)



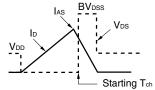
ELECTRICAL CHARACTERISTICS (TA = 25°C)

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CHARACTERISTICS	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±16 V, V _{DS} = 0 V			±100	nA
Gate to Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		3.0	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 5 V, I _D = 12 A	9	19		S
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = 10 V, I _D = 30 A		7.2	8.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 20 A		10.4	14	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		1200		pF
Output Capacitance	Coss	V _{GS} = 0 V,		180		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		100		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 30 A,		14		ns
Rise Time	tr	V _{GS} = 10 V,		11		ns
Turn-off Delay Time	t _{d(off)}	R _G = 3 Ω		43		ns
Fall Time	tf			10		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		24		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V,		3		nC
Gate to Drain Charge	Q _{GD}	ID = 30 A	_	7		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	IF = 30 A, VGS = 0 V		0.89	1.5	V
Reverse Recovery Time	trr	IF = 30 A, VGS = 0 V,		21		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A /μs		12		nC

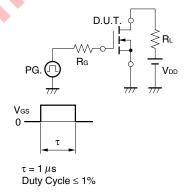
Note Pulsed

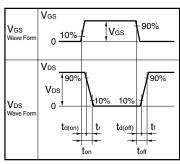
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c} \text{D.U.T.} \\ \text{Rg} = 25 \ \Omega \\ \text{PG.} \\ \text{$>$50 \ \Omega$} \\ \end{array}$



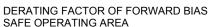
TEST CIRCUIT 2 SWITCHING TIME

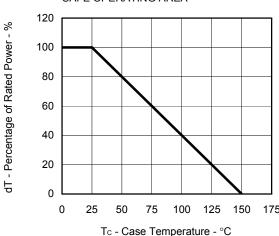




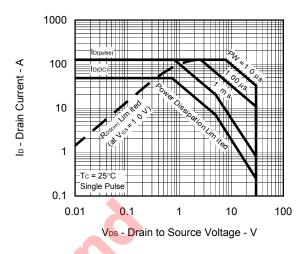
TEST CIRCUIT 3 GATE CHARGE

TYPICAL CHARACTERISTICS (TA = 25°C)

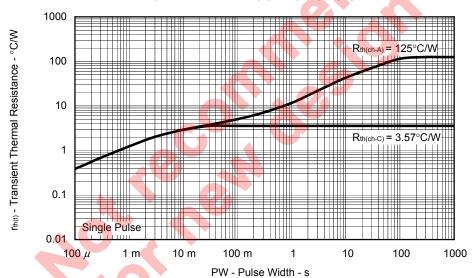




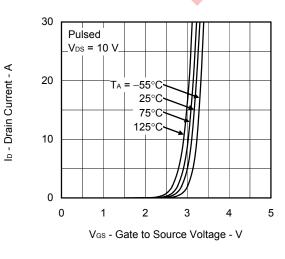
FORWARD BIAS SAFE OPERATING AREA



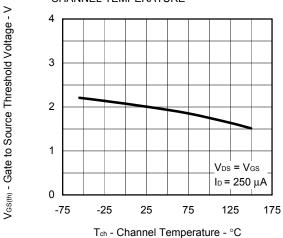
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

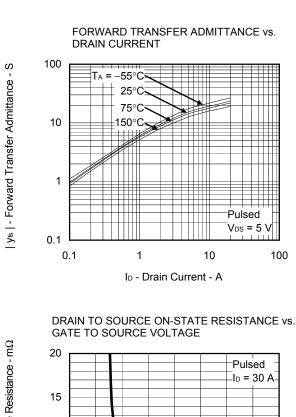


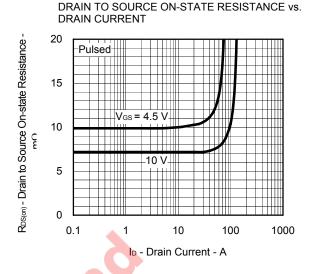
FORWARD TRANSFER CHARACTERISTICS

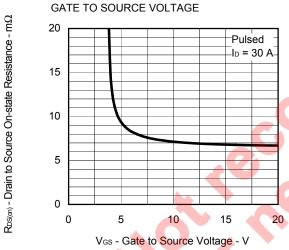


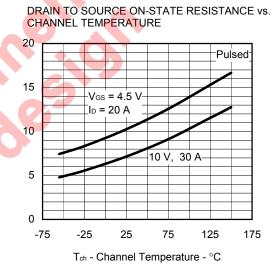
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE

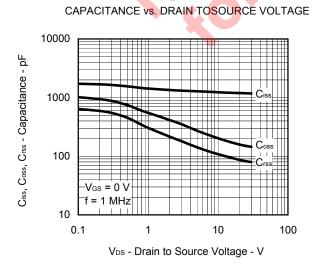


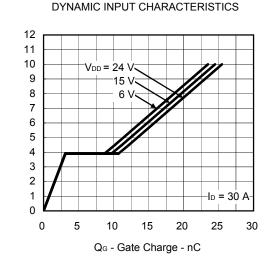








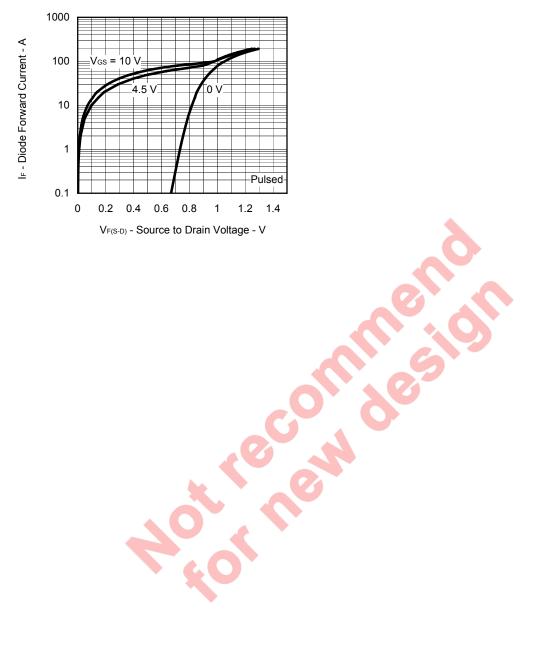




RDS(m) - Drain to Source On-state Resistance

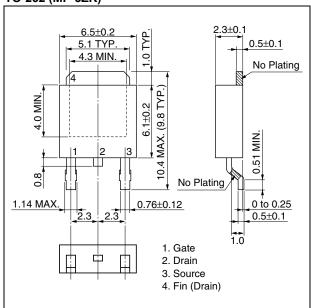
Ves - Gate to Source Voltage - V

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

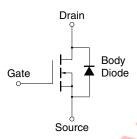


PACKAGE DRAWINGS (Unit: mm)

TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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